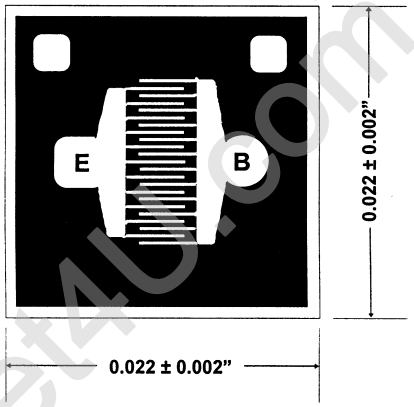
PNP SILICON HIGH FREQUENCY TRANSISTOR

DESCRIPTION:

The **2N5583** is Designed for High Frequency Amplifier, and Non Saturated Switching Applications.

PACKAGE STYLE



MAXIMUM RATINGS

I_C	500 mA
V_{CE}	-30 V
P_{DISS}	1.0 W @ T_A = 25 °C 5.0 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	350 °C/W

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 10 mA	-30			V
BV_{CBO}	I_C = 10 µA	-30			V
BV_{EBO}	I_C = 100 µA	-3.0			V
I_{CBO}	V_{CB} = -20 V			50	nA
I_{EBO}	V_{EB} = -2.0 V			500	nA
h_{FE}	V_{CE} = -2.0 V I_C = 40 mA I_C = 100 mA V_{CE} = -5.0 V I_C = 300 mA	20 25 15		100	---
$V_{CE(SAT)}$	I_C = 100 mA I_B = 10 mA			-0.8	V
$V_{BE(ON)}$	V_{CE} = -2.0 V I_C = 100 mA			-1.8	V
f_t	V_{CE} = -10 V I_C = 40 mA f = 100 MHz I_C = 100 mA f = 100 MHz	1000 1300			MHz
C_{cb}	V_{CB} = -15 V f = 100 KHz			5.0	pF
C_{eb}	V_{EB} = -0.5 V f = 100 KHz			35	pF
$r_{b'C_c}$	V_{CB} = -10 V I_C = 50 mA f = 63.6 MHz		8.2		pS
t_d t_r t_f	V_{CC} = -31.4 V I_C = 150 mA R_C = 160 Ω R_E = 26.6 Ω		1.2 2.2 2.0		nS